



TAYCHIPST

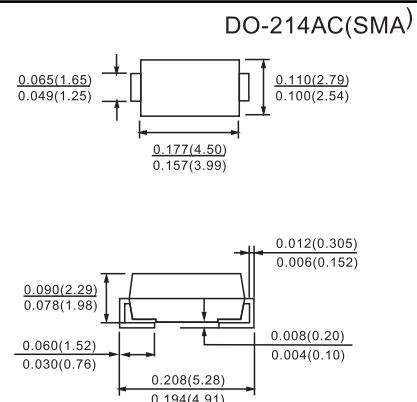
Silicon Mesa SMD Rectifier

BYG10D THRU BYG10M

200V-1000V 1.5A

FEATURES

- Controlled avalanche characteristics
- Glass passivated junction
- Low reverse current
- High surge current capability
- Wave and reflow solderable



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**Absolute Maximum Ratings**

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage =Repetitive peak reverse voltage		BYG10D	$V_R=V_{RRM}$	200	V
		BYG10G	$V_R=V_{RRM}$	400	V
		BYG10J	$V_R=V_{RRM}$	600	V
		BYG10K	$V_R=V_{RRM}$	800	V
		BYG10M	$V_R=V_{RRM}$	1000	V
Peak forward surge current	$t_p=10\text{ms}$, half sinewave		I_{FSM}	30	A
Average forward current			I_{FAV}	1.5	A
Junction and storage temperature range			$T_j=T_{stg}$	-55...+150	°C
Pulse energy in avalanche mode, non repetitive (inductive load switch off)	$I_{(BR)R}=1\text{A}$, $T_j=25^\circ\text{C}$		E_R	20	mJ

Maximum Thermal Resistance

Parameter	Test Conditions	Symbol	Value	Unit
Junction lead	$T_L=\text{const.}$	$R_{th JL}$	25	K/W
Junction ambient	mounted on epoxy-glass hard tissue	$R_{th JA}$	150	K/W
	mounted on epoxy-glass hard tissue, 50mm^2 $35\mu\text{m}$ Cu	$R_{th JA}$	125	K/W
	mounted on Al-oxid-ceramic (Al_2O_3), 50mm^2 $35\mu\text{m}$ Cu	$R_{th JA}$	100	K/W

Electrical Characteristics

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=1\text{A}$		V_F			1.1	V
	$I_F=1.5\text{A}$		V_F			1.15	V
Reverse current	$V_R=V_{RRM}$		I_R			1	μA
	$V_R=V_{RRM}$, $T_j=100^\circ\text{C}$		I_R			10	μA
Reverse recovery time	$I_F=0.5\text{A}$, $I_R=1\text{A}$, $i_R=0.25\text{A}$		t_{rr}			4	μs



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RATINGS AND CHARACTERISTIC CURVES

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